**Product data sheet** 

## 1. General description

NPN low  $V_{CEsat}$  Breakthrough in Smal Signal (BISS) transitor in a medium power SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

#### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub>
- High collector current capability I<sub>C</sub> and I<sub>CM</sub>
- · High energy efficiency due to less heat generation
- AEC-Q101 qualified

## 3. Applications

- DC-to-DC conversion
- · Supply line switches
- · Battery charger
- · LCD backlighting
- Driver in low supply voltage applications (e.g. lamps and LEDs)
- · Inductive load driver (e.g. relays, buzzers and motors)

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-	60	V
I <sub>C</sub>	collector current			-	-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-	2	Α
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; $T_{amb}$ = 25 °C	[1]	170	-	360	

[1] Pulse test:  $t_p \le 300 \ \mu s$ ;  $\delta \le 0.02$ 



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# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	E	emitter		С
2	С	collector		В
3	В	base	3 2 1	E
			SOT89	sym123

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package				
	Name	Description	Version		
PBSS4160X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89		

# 7. Marking

#### Table 4. Marking codes

Type number	Marking code
PBSS4160X	S41

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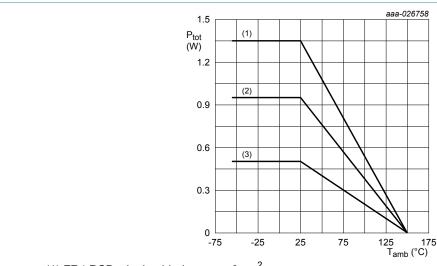
## 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	60	V
$V_{CEO}$	collector-emitter voltage	open base		-	60	V
$V_{EBO}$	emitter-base voltage	open collector		-	7	V
I <sub>C</sub>	collector current			-	1	Α
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	2	Α
I <sub>B</sub>	base current			-	300	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$		-	1	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	500	mW
			[2]	-	950	mW
			[3]	-	1.35	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>. Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.



- (1) FR4 PCB, single-sided copper, 6 cm<sup>2</sup>
- (2) FR4 PCB, single-sided copper, 1 cm<sup>2</sup>
- (3) FR4 PCB, single-sided copper, standard footprint

Fig. 1. Power derating curves

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### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>		in free air	[1]	-	-	250	K/W
from junction to ambient			[2]	-	-	132	K/W
		[3]	-	-	93	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 1 cm<sup>2</sup>.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated; mounting pad for collector 6 cm<sup>2</sup>.

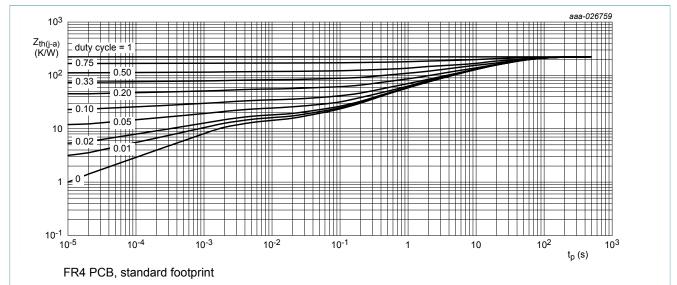


Fig. 2. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

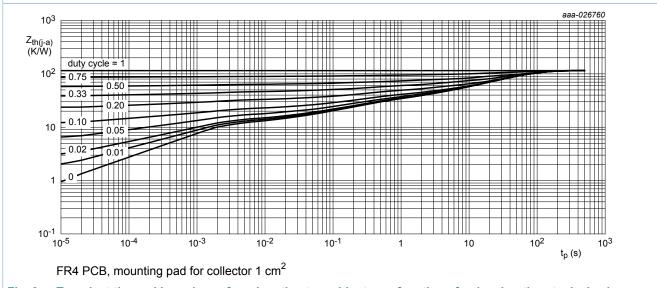
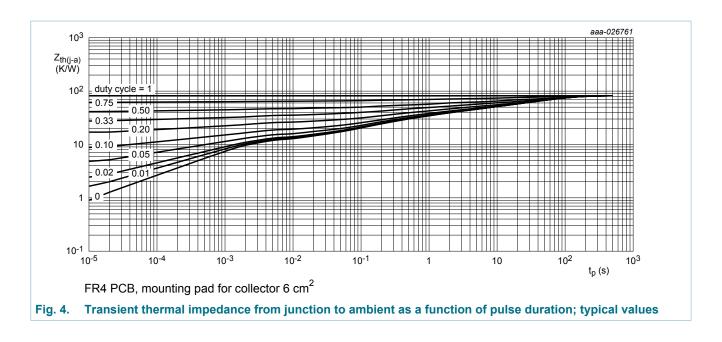


Fig. 3. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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#### 60 V, 1 A NPN low VCEsat BISS transistor



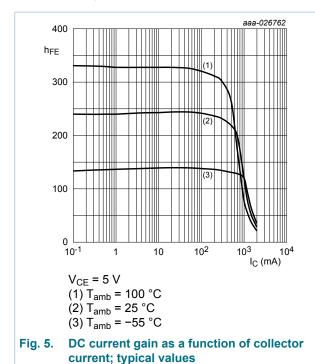
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### 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base cut-off	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C		-	-	100	nA
	current	V <sub>CB</sub> = 48 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C		-	-	10	μΑ
I <sub>CES</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 48 V; V <sub>BE</sub> = 0 V; T <sub>amb</sub> = 25 °C		-	-	100	nA
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ A}; T_{amb} = 25 \text{ °C}$		-	-	100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = 10 V; $I_{C}$ = 500 mA; $T_{amb}$ = 25 °C	[1]	170	-	360	
		V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	[1]	50	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}; T_{amb} = 25 \text{ °C}$	[1]	-	-	200	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance			-	-	0.4	Ω
V <sub>BEsat</sub>	base-emitter saturation voltage		[1]	-	-	1.2	V
$V_{BE}$	base-emitter voltage	V <sub>CE</sub> = 5 V; I <sub>C</sub> = 1 A; T <sub>amb</sub> = 25 °C	[1]	-	-	1	V
f <sub>T</sub>	transition frequency	$V_{CE}$ = 10 V; $I_{C}$ = 50 mA; f = 100 MHz; $T_{amb}$ = 25 °C		-	180	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = 10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C		-	6	-	pF

#### [1] Pulse test: $t_p \le 300 \ \mu s; \ \delta \le 0.02$



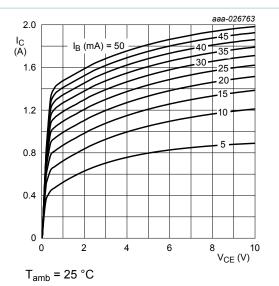


Fig. 6. Collector current as a function of collectoremitter voltage; typical values

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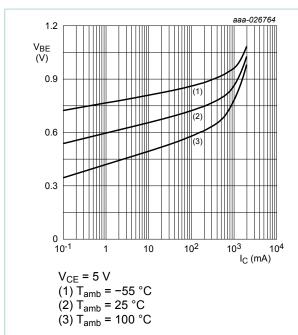


Fig. 7. Base-emitter voltage as a function of collector current; typical values

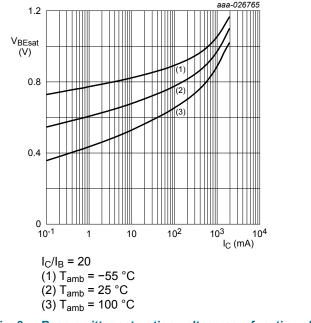
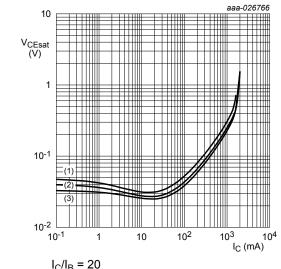
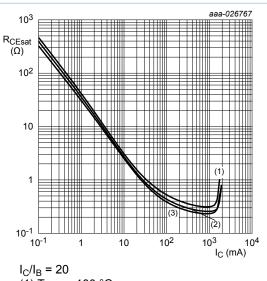


Fig. 8. Base-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ (1)  $T_{\rm amb} = 100~{\rm ^{\circ}C}$ (2)  $T_{\rm amb} = 25~{\rm ^{\circ}C}$ (3)  $T_{\rm amb} = -55~{\rm ^{\circ}C}$ 

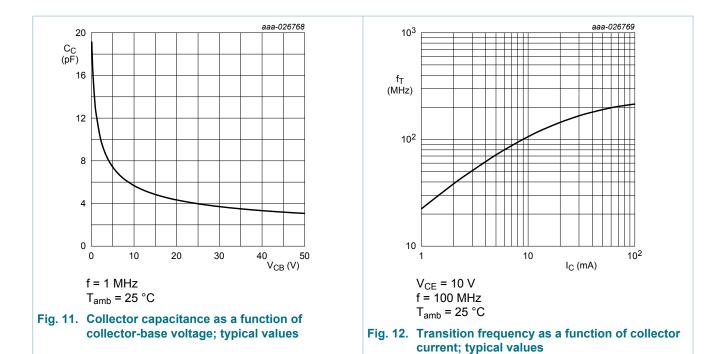
Fig. 9. Collector-emitter saturation voltage as a function of collector current; typical values



I<sub>C</sub>/I<sub>B</sub> = 20 (1) T<sub>amb</sub> = 100 °C (2) T<sub>amb</sub> = 25 °C (3) T<sub>amb</sub> = -55 °C

Fig. 10. Collector-emitter saturation resistance as a function of collector current; typical values

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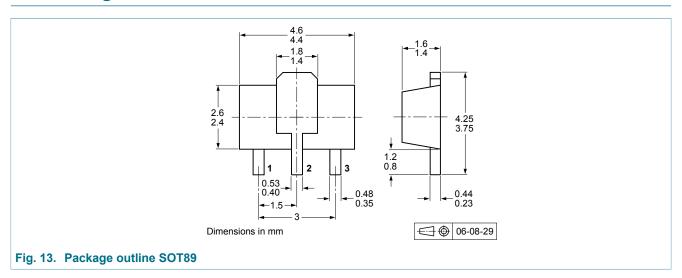


### 11. Test information

#### **Quality information**

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

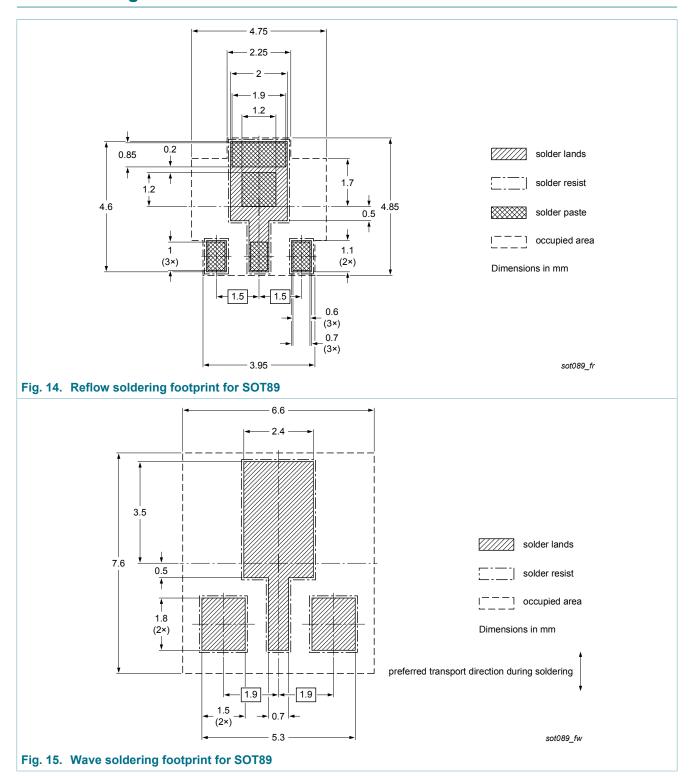
## 12. Package outline



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### 60 V, 1 A NPN low VCEsat BISS transistor

## 13. Soldering



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# 14. Revision history

### **Table 8. Revision history**

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160X v.1	20170523	Product data sheet	-	-

#### 60 V, 1 A NPN low VCEsat BISS transistor

# 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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	General description

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